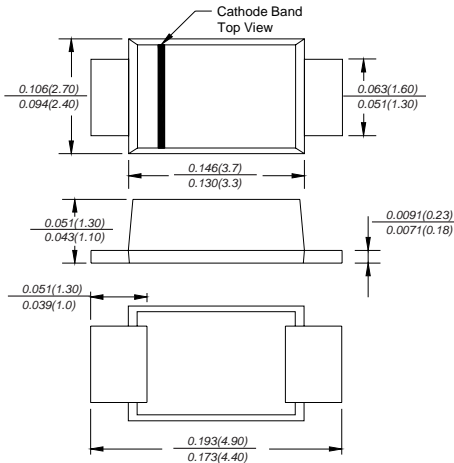




RS1AF THRU RS1MF

SURFACE MOUNT FAST RECOVERY RECTIFIER
 Reverse Voltage - 50 to 1000 Volts Forward Current - 1.0 Ampere

SMAF



Dimensions in inches and (millimeters)

FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Fast switching for high efficiency
- ◆ Low reverse leakage
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed: 260°C/10 seconds at terminals
- ◆ Glass passivated chip junction

MECHANICAL DATA

Case: JEDEC SMAF molded plastic body over passivated chip
Terminals: Solder plated, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: 0.0018 ounce, 0.064 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

MDD Catalog Number	SYMBOLS	RS1AF	RS1BF	RS1DF	RS1GF	RS1JF	RS1KF	RS1MF	UNITS
Marking code		MDD RS1AF	MDD RS1BF	MDD RS1DF	MDD RS1GF	MDD RS1JF	MDD RS1KF	MDD RS1MF	
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at $T_L=90^\circ\text{C}$	$I_{(AV)}$	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30.0							Amps
Maximum instantaneous forward voltage at 1.0A	V_F	1.3							Volts
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$	I_R	5.0 50.0							μA
Maximum reverse recovery time (NOTE 1)	t_{rr}	150			250		500		ns
Typical junction capacitance (NOTE 2)	C_J	15.0							pF
Typical thermal resistance (NOTE 3)	$R_{\theta JA}$	50.0							$^\circ\text{C}/\text{W}$
Operating junction and storage temperature range	T_J, T_{STG}	-50 to +150							$^\circ\text{C}$

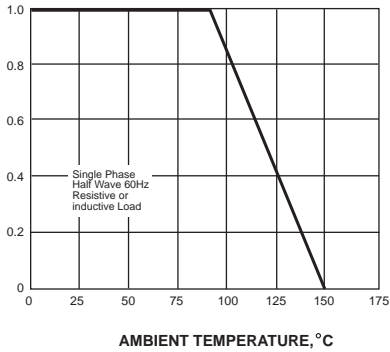
Note: 1. Reverse recovery condition $I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas



RATINGS AND CHARACTERISTIC CURVES RS1AF THRU RS1MF

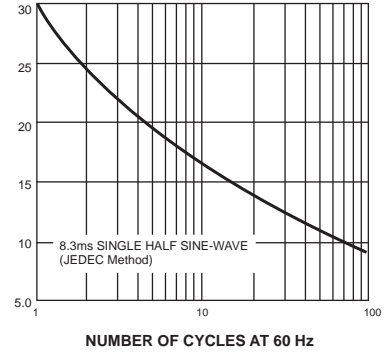
AVERAGE FORWARD RECTIFIED CURRENT,
AMPERES

FIG. 1- FORWARD CURRENT DERATING CURVE



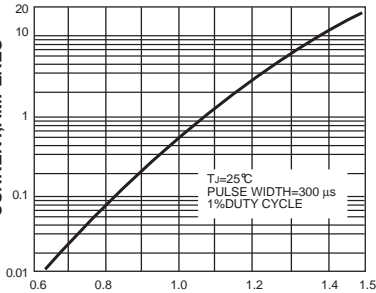
PEAK FORWARD SURGE CURRENT,
AMPERES

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



INSTANTANEOUS FORWARD CURRENT, AMPERES

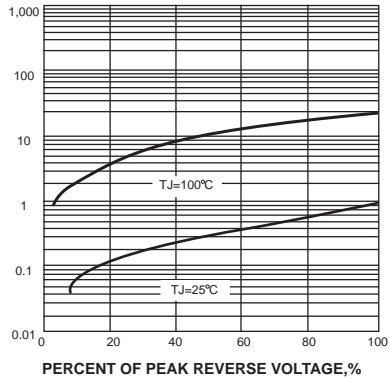
FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



INSTANTANEOUS FORWARD VOLTAGE,
VOLTS

INSTANTANEOUS REVERSE CURRENT,
MICROAMPERES

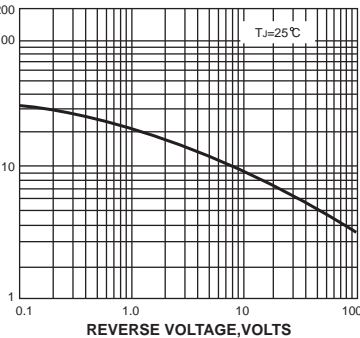
FIG. 4-TYPICAL REVERSE CHARACTERISTICS



PERCENT OF PEAK REVERSE VOLTAGE, %

JUNCTION CAPACITANCE, pF

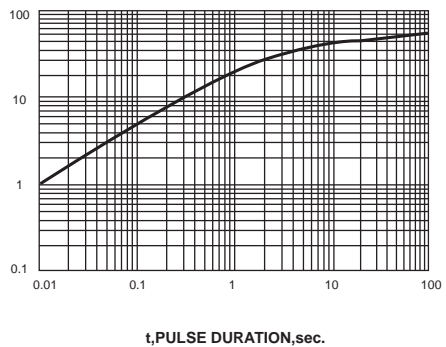
FIG. 5-TYPICAL JUNCTION CAPACITANCE



REVERSE VOLTAGE, VOLTS

TRANSIENT THERMAL IMPEDANCE,
°C/W

FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE



t, PULSE DURATION, sec.

The cruve graph is for reference only, can't be the basis for judgment(曲线图仅供参考!)



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